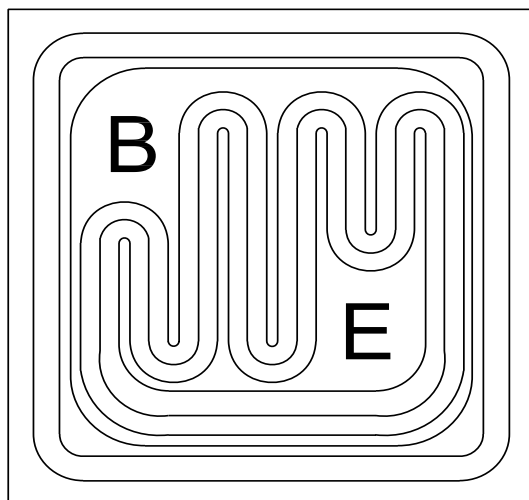


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	106 x 106 MILS
Die Thickness	12 MILS
Base Bonding Pad Area	25 x 33 MILS
Emitter Bonding Pad Area	30 x 36 MILS
Top Side Metallization	Al 50,000Å
Back Side Metallization	Ag 10,000Å

GEOMETRY

BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

950

PRINCIPAL DEVICE TYPES

2N3055

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